



erial FEPROM



Three-wire Serial EEPROM

2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

Features

► Low-voltage Operation

-1.8V (Vcc = 1.8V to 5.5V)

►Three-wire Serial Interface

► Sequential Read Operation

▶2 MHz Clock Rate (5V) Compatibility

► Self-timed Write Cycle (5 ms max)

► High-reliability

- Endurance: 1 Million Write Cycles

- Data Retention: 100 Years

▶8-lead PDIP/SOP/MSOP/TSSOP, 8-pad DFN, packages

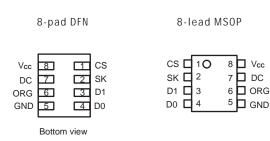
■ General Description

The K93C56/66 provides 2048/4096 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 128/256 words of 16 bits each, when the ORG pin is connected to VCC and 256/512 words of 8 bits each when it is tied to ground. The K93C56/66 is available in space-saving 8-lead PDIP, 8-lead SOP, 8-lead TSSOP, 8-lead MSOP, and 8-pad DFN packages. The K93C56/66 is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a Read instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate erase cycle is required before write. The Write cycle is only enabled when it is in the Erase/Write Enable state. When CS is brought "high" following the initiation of a write cycle, the DO pin outputs the Ready/Busy status.

■ Pin Configuration

► Table 1: Pin Configuration

Pin Name	Founctions
CS	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
Vcc	Power Supply
ORG	Internal Organization
DC	Don't Connect



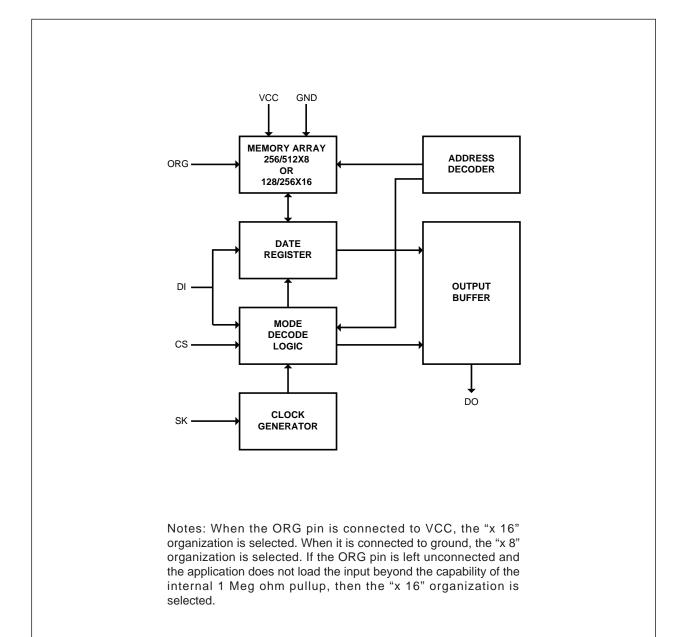
8-lead PDIP 8-lead SOP 8-lead TSSOP cs **1**0 cs 🗖 10 cs □ ☐ Vcc 8 D Vcc 8 Vcc 7 DC SK **□** 2 7 DC 7 DC sk □ SK 🗖 2 2 D1 D1 🗖 3 6 G ORG D1 🗖 3 6 D ORG 3 6 D ORG D0 🗖 D0 🗀 ☐ GND D0 GND GND GND

Spring 2012 V1.3 .001.



Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

■ Block Diagram



V1.3 Spring 2012 .002.







■ Function Descriptions

The K93C56/66 is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. A valid instruction starts with a rising edge of CS and consists of a start bit (logic"1") followed by the appropriate op code and the desired memory address location.

► Table 2: Instruction Set for the K93C56/66

Instruction	SB	OP Code	Add	lress	Da	ata	Comments
IIISHUCHOH	SD	OF Code	x8	x16	x8	x16	Confinence
READ	1	10	A8 - A0	A7 - A0			Reads data stored in memory, at specified address
EWEN	1	00	11XXXXXXX	11XXXXXX			Write enable must precede all programming modes
ERASE	1	11	A8 - A0	A7 - A0			Erase memory location An - A0
WRITE	1	01	A8 - A0	A7 - A0	D7 - D0	D15 - D0	Writes memory location An - A0
ERAL	1	00	10XXXXXXX	10XXXXXX			Erases all memory locations. Valid only at Vcc = 4.5V to 5.5V
WRAL	1	00	01XXXXXXX	01XXXXXX	D7 - D0	D15 - D0	Writes all memory locations. Valid only at $Vcc = 4.5V$ to $5.5V$
EWDS	1	00	00XXXXXXX	00XXXXXX			Disables all programming instructions

Notes: The X's in the address field represent don't care values and must be clocked.

READ (READ): The Read (READ) instruction contains the address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 8- or 16-bit data output string. The K93C56/66 supports sequential read operations. The device will automatically increment the internal address pointer and clock out the next memory location as long as Chip Select (CS) is held high. In this case, the dummy bit (logic "0") will not be clocked out between memory locations, thus allowing for a continuous steam of data to be read.

ERASE/WRITE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable(EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the EWEN state, programming remains enabled until an EWDS instruction is executed or Vcc power is removed from the part.

ERASE (ERASE): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 8 or 16 bits of data to be written into the specified memory location. The self-timed programming cycle, tWP, starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. A Ready/Busy status cannot be obtained if the CS is brought high after the end of the selftimed programming cycle, TWP.

ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). The ERAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

Spring 2012 .003.





2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

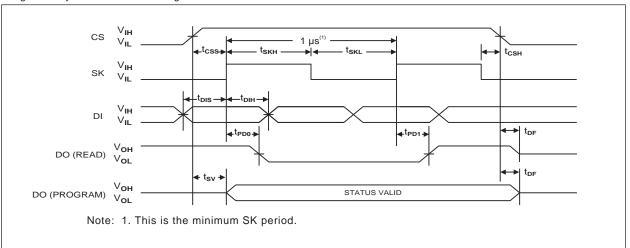
■ Function Descriptions

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). The WRAL instruction is valid only at $Vcc = 5.0V \pm 10\%$.

ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the Read instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

■ Timing Diagrams

► Figure 1: Synchronous Data Timing



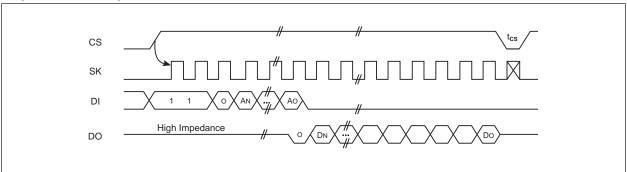
▶Table 3: Organization Key for Timing Diagram

I/O	K93C	56(2K)	K93C66(4K)		
110	X 8	X 16	X 8	X 8	
AN	A8(1)	A7(2)	A8	A7	
DN	D7	D15	D7	D15	

Note: 1. A8 is a DON'T CARE value, but the extra clock is required.

2. A7 is a DON'T CARE value, but the extra clock is required.

▶ Figure 2: READ Timing



Spring 2012 .004.

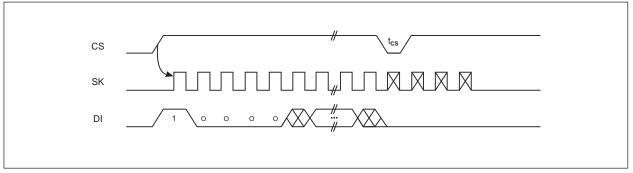


Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

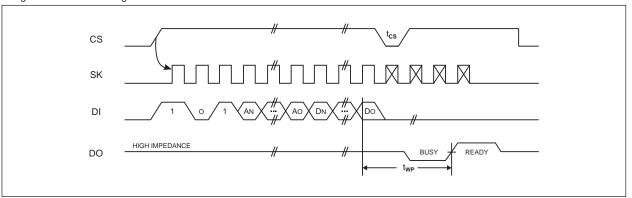
■ Timing Diagrams

▶ Figure 3: EWEN Timing CS SK DI

▶ Figure 4: EWDS Timing



▶ Figure 5: WRITE Timing



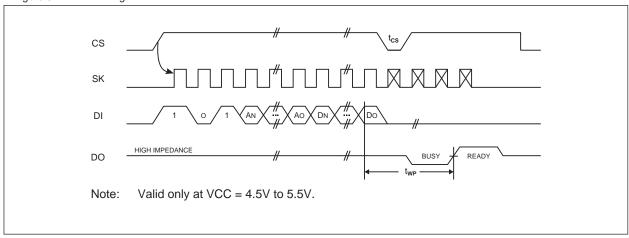
V1.3 Spring 2012 .005.



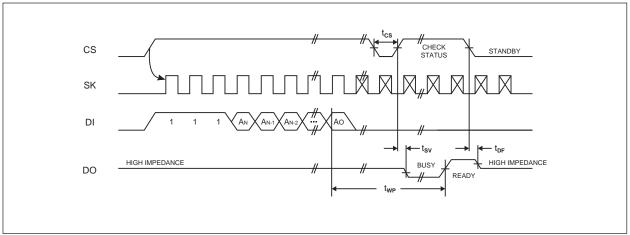
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

■ Timing Diagrams

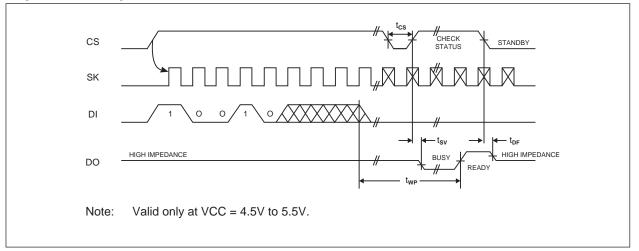
► Figure 6: WRAL Timing



▶ Figure 7: ERASE Timing



▶ Figure 8: ERAL Timing



V1.3 Spring 2012 .006.





■ Electrical Characteristics

► Absolute Maximum Ratings

DC Supply Voltage -0.3V to +6.5V

Input / Output Voltage GND-0.3V to Vcc+0.3V

Operating Ambient Temperature -40°C to +85°C

Storage Temperature -65°C to +150°C

▶ Comments

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

■ DC Characteristics

► Applicable over recommended operating range from: T_A = -40°C to +85°C, V_{CC} = + 1.8V to + 5.5V,(unless otherwise noted)

Symbol	Parameter	Test Con	dition	Min	Тур	Max	Units
V _{CC1}	Supply Voltage	-		1.8	-	5.5	V
V_{CC2}	Supply Voltage	-		2.7	-	5.5	V
Vcc3	Supply Voltage	-		4.5	-	5.5	V
Icc	Supply Current	Vcc = 5.0V	Read at 1.0 MHz	-	0.5	2.0	mA
ICC	Supply Current	VCC = 5.0V	Write at 1.0 MHz	-	2	3.0	mA
I _{SB1}	Standby Current	Vcc = 1.8V	CS = 0V	-	-	1.0	μΑ
I _{SB2}	Standby Current	Vcc = 2.7V	CS = 0V	-	-	1.0	μA
I _{SB3}	Standby Current	Vcc = 5.0V	CS = 0V	-	-	1.0	μΑ
I _{IL(1)}	Input Leakage	Vin = 0V	to Vcc	-	0.1	1.0	μA
I _{IL(2)}	Input Leakage	Vin = 0V	to Vcc	-	2.0	3.0	μΑ
loL	Output Leakage	Vin = 0V	to Vcc	-	0.1	1.0	μA
V _{IL1(3)}	Input Low Voltage	2.7V ≤ Vc	c < 5.5V	-0.3	-	0.8	
V _{IH1(3)}	Input High Voltage	2.7 V < VC	C ≈ 3.3 V	2.0	-	Vcc + 0.3	V
V _{IL2(3)}	Input Low Voltage	101/ - 1/0	o < 2.7\/	-0.5	-	Vcc + 0.3	
$V_{\text{IH}_{2(3)}}$	Input High Voltage	1.8V ≤ Vcc ≤ 2.7V		Vcc x 0.7	-	Vcc + 0.3	V
V _{OL1}	Output Low Voltage	2.7V ≤ Vcc ≤ 5.5V	IOL = 2.1mA	-	-	0.4	V
Vон1	Output High Voltage	2.7 V = VCC = 3.5 V	IOH = -0.4mA	2.4	-		V
V _{OL2}	Output Low Voltage	1.8V ≤ Vcc ≤ 2.7V	IOL = 0.15mA	-	-	0.2	V
V _{OH2}	Output High Voltage	1.0V \(\times \times \times \(2.7V \)	$IOH = -100\mu A$	Vcc-0.2	-	-	V

Note: VIL min and VIH max are reference only and are not tested.

■ Pin Capacitance

► Applicable over recommended operating range from TA = 25°C, f = 1.0 MHz, Vcc = +1.8V (unless otherwise noted)

Symbol	Test Conditions	Max	Unit	Conditions
COUT	Output Capacitance (DO)	5	pF	VOUT = 0V
CIN	Input Capacitance (CS, SK, DI, ORG)	5	pF	VIN = 0V

Spring 2012 .007.



Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

■ AC Characteristics

►Applicable over recommended operating range from TA = -40°C to +85°C, Vcc = + 1.8V to + 5.5V

CL = 1 TTL G	ate and 100pF	(unless otherwise noted)
--------------	---------------	--------------------------

Symbol	Parameter	Test Co	ondition	Min	Тур	Max	Units
		4.5V ≤ V	/cc ≤ 5.5V	0		2	
fsк	SK Clock Frequency	2.7V ≤ V	cc ≤ 5.5V	0	-	1	MHz
		1.8V ≤ V	/cc ≤ 5.5V	0		0.25	
		4.5V ≤ V	/cc ≤ 5.5V	250			
tsкн	SK High Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	/cc ≤ 5.5V	1000			
		4.5V ≤ V	/cc ≤ 5.5V	250			
tskl	SK Low Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	/cc ≤ 5.5V	1000			
		4.5V ≤ V	/cc ≤ 5.5V	250			
tcs	Minimum CS Low Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	cc ≤ 5.5V	1000			
			4.5V ≤ Vcc ≤ 5.5V	50			
tcss	CS Setup Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	50	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	200			
			4.5V ≤ Vcc ≤ 5.5V	100			
tois	DI Setup Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	100	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	400			
tсsн	CS Hold Time	Relative to SK		0	-	-	ns
			4.5V ≤ Vcc ≤ 5.5V	100			
tын	DI Hold Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	100	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	400			
			4.5V ≤ Vcc ≤ 5.5V			250	
t _{PD1}	Output Delay to "1"	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
			4.5V ≤ Vcc ≤ 5.5V			250	
t _{PD0}	Output Delay to "0"	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
			4.5V ≤ Vcc ≤ 5.5V			250	
tsv	CS to Status Valid	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
	CS to DO in High	AC Toot	4.5V ≤ Vcc ≤ 5.5V			100	
tor	CS to DO in High	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	100	ns
	Impedance	CS = VIL	1.8V ≤ Vcc ≤ 5.5V			400	
twp	Write Cycle Time	-	-	-	1.5	5	ms
Endurance ⁽¹⁾	5.0V, 25°C		-	1M	-	-	Write Cycle

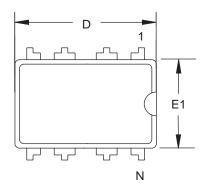
Note: 1. This parameter is characterized and is not 100% tested.

V1.3 Spring 2012 .008.

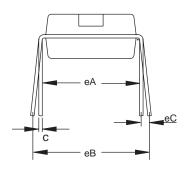
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



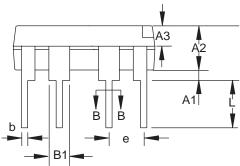
■ 8-lead PDIP package diagram



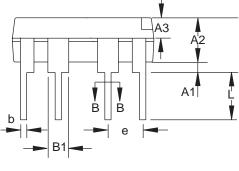
Top View



End View



Side View



Base Metal With Plating

Section B-B

COMMON DIMENSIONS

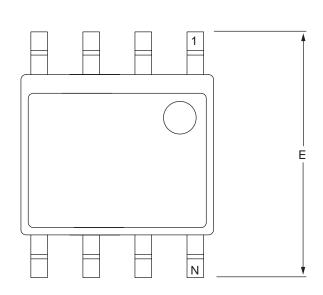
(Unit of Measure = mm)

SYMBOL	MIN	MAX		
Α	3.60	4.00		
A1	0.51	-		
A2	3.10	3.50		
А3	1.50	1.70		
b	0.44	0.53		
b1	0.43 0.48			
В	1.52 BSC			
С	0.25	0.31		
c1	0.24	0.26		
D	9.05	9.45		
E1	6.15	6.55		
е	2.54 BSC			
eA	7.62 BSC			
eB	7.62 9.50			
eC	0 0.94			
L	3.00	-		

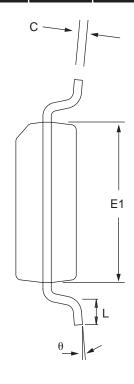
V1.3 Spring 2012 .009.

Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

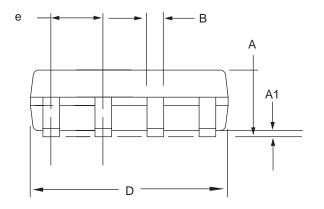
■ 8-lead SOP package diagram



Top View



End View



Side View

COMMON DIMENSIONS

(Unit of Measure = mm)

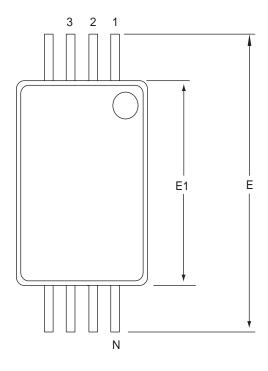
SYMBOL	MIN	MAX		
А	1.35	1.75		
A1	0.10	0.25		
b	0.31	0.51		
С	0.17	0.25		
D	4.70	5.10		
E1	3.80	4.00		
E	5.79	6.20		
е	1.27 BSC			
L	0.40	1.27		
θ	0°	8°		

V1.3 Spring 2012 .010.

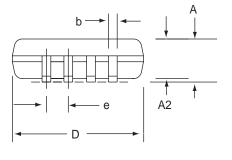
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



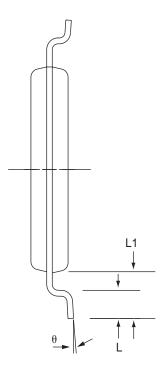
■ 8-lead TSSOP package diagram



Top View



Side View



End View

COMMON DIMENSIONS

(Unit of Measure = mm)

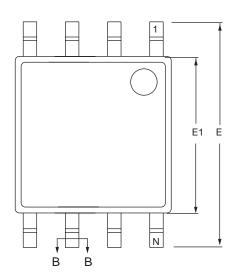
	•	<u> </u>		
SYMBOL	MIN	MAX		
D	2.80	3.20		
Е	6.20	6.60		
E1	4.20	4.60		
А	-	1.20		
A2	A2 0.80 1.15			
b	0.19 0.30			
е	0.65 BSC			
L	0.45	0.75		
L1	1.00 BSC			
θ	0°	8°		

V1.3 Spring 2012 .011.

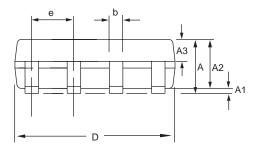
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



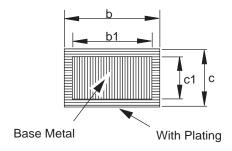
■ 8-lead MSOP package diagram



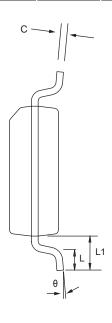
Top View



Side View



Section B-B



End View

COMMON DIMENSIONS

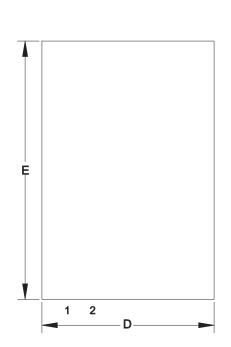
(Unit of Measure = mm)

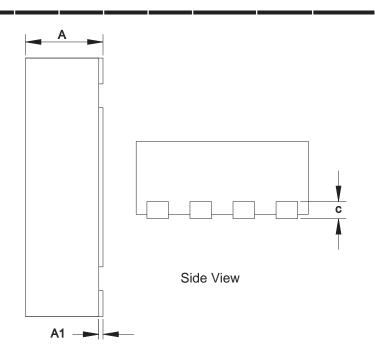
SYMBOL	MIN	MAX		
А	-	1.10		
A1	0.05	0.15		
A2	0.75	0.95		
A3	0.30	0.40		
b	0.29	0.38		
b1	0.28	0.33		
С	0.15	0.20		
c1	0.14	0.16		
D	2.90	3.10		
Е	4.70	5.10		
E1	2.90	3.10		
е	0.65 BSC			
L	0.40	0.70		
L1	0.95 BSC			
θ	0°	8°		

V1.3 Spring 2012 .012.

Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

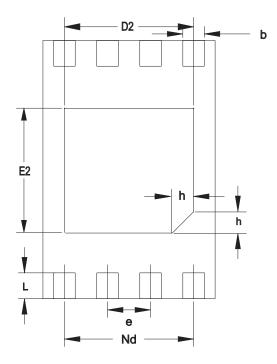
■ 8-pad DFN package diagram





Top View

End View



Bottom View

COMMON DIMENSIONS (Unit of Measure = mm)

SYMBOL	MIN	MAX		
А	0.70	0.80		
A1	-	0.05		
b	0.18	0.30		
С	0.18	0.25		
D	1.90	2.10		
D2	1.50	REF		
е	0.50 BSC			
Nd	1.50	BSC		
E	2.90	3.10		
E2	1.60 BSC			
L	0.30 0.50			
h	0.20	0.30		

V1.3 Spring 2012 .013.



8.Operating Voltage

A = 1.8 to 5.5 V



Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

■ Ordering Information

Product Name: Κ 93 XXXPart Number: $X \quad X \quad X \quad X$ Χ 93 Κ XXX 8 (version) 2 3 4 5 6 7 1.Prefix 4.Package Type 5.Temperature Range 7.Plating Technology D = PDIPBlank = Standard SnPb plating $I = Industry (-40^{\circ}C to +85^{\circ}C)$ 2.Series Name S = SOPG = RoHS compliant 93: Three-wire (SPI) Interface 6.Pack Type T = TSSOPS = Green, level 1 T = Tube 3.EEPROM Density M = MSOPX = Green, level 3 R = Tape & Reel C56 = 2K bits

N = DFN

■ Available package types

C66 = 4K bits

Model	PDIP	SOP	TSSOP	MSOP	DFN
K93C56	V	V	V	V	V
K93C66	\checkmark	\checkmark	V	V	V

■ Product Datasheet Change Notice

Datasheet Revision History				
Version	Content	Date		
1.0	Initial version	Dec., 2008		
1.1	Package type update	Jan., 2011		
1.2	Ordering information update	May, 2011		
1.3	Ordering information update	Jan., 2012		

V1.3 Spring 2012 .014.

Three-wire Serial EEPROM

2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



Disclaimers

The information in this publication has been carefully checked and is believed to be entirely accurate at the time of publication. HUAJIE assumes no responsibility, however, for possible errors or omissions, or for any consequences resulting from the use of the information contained herein.

HUAJIE reserves the right to make changes in its products or product specifications with the intent to improve function or design at any time and without notice and is not required to update this documentation to reflect such changes.

This publication does not convey to a purchaser of semiconductor devices described herein any license under the patent rights of HUAJIE or others.

HUAJIE makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does HUAJIE assume any liability arising out of the application or use of any product or circuit and specifically disclaims any and all liability, including without limitation any consequential or incidental damages.

" Typ. " parameters can and do vary in different applications. All operating parameters, including " Typ. " must be validated for each customer application by the customer's technical experts.

HUAJIE products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, for other applications intended to support or sustain life, or for any other application in which the failure of the HUAJIE product could create a situation where personal injury or death may occur.

Should the Buyer purchase or use a HUAJIE product for any such unintended or unauthorized application, the Buyer shall indemnify and hold HUAJIE and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, expenses, and reasonable attorney fees arising out of, either directly or indirectly, any claim of personal injury or death that may be associated with such unintended or unauthorized use, even if such claim alleges that HUAJIE was negligent regarding the design or manufacture of said product.

K93C Series (SPI Bus) Serial EEPROM Data Sheet, Revision 1.3

2012 HUAJIE

All rights reserved. No part of this publication may be reproduced, stored in a retrieval system, or transmitted in any form or by any means, electric or mechanical, by photocopying, recording, or otherwise, without the prior written consent of HUAJIE.

Spring 2012 .015.